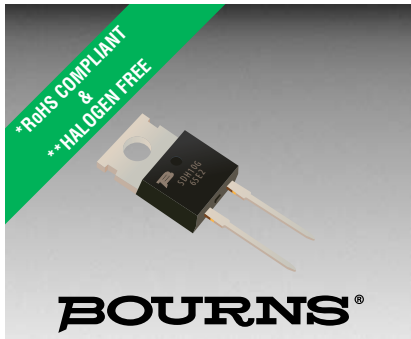




Features

- High efficiency with low power loss
- Low reverse leakage current
- High peak forward surge current (I_{FSM})
- Reduced EMI
- Maximum operating T_J up to 175 °C
- Epoxy compound is flame retardant to the UL 94V-0 standard
- RoHS compliant*, Pb free and halogen free**

Applications

- Switched-Mode Power Supplies (SMPS)
- Power Factor Correction (PFC)
- PV inverters
- DC-DC converters
- Telecommunications
- Motor drives

BSDH10G65E2 Silicon Carbide Schottky Diode

General Information

Bourns® Model BSDH10G65E2 Silicon Carbide (SiC) Schottky Diode provides excellent current carrying capacity. This advanced, high efficiency power component is suitable for applications such as converters requiring a high peak forward surge capability, low forward voltage drop, reduced thermal resistance and low power loss.

Bourns offers Silicon Carbide Schottky Diodes for rectification applications in assorted styles. The Model BSDH10G65E2 is available in a TO220-2 package, well-suited for high frequency Switched-Mode Power Supplies.

Additional Information

Click these links for more information:



Absolute Maximum Ratings (@ $T_J = 25\text{ °C}$ Unless Otherwise Noted)

Parameter	Symbol	BSDH10G65E2	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	650	V
Average Forward Current (Square Wave Pulse, $D = 0.5$, $T_{mb} \leq 130\text{ °C}$, Fig. Zth(J-mb))	$I_{F(AV)}$	10	A
Repetitive Peak Forward Current (Square Wave Pulse, $D = 0.5$, $T_{mb} \leq 130\text{ °C}$, $t_p = 25\text{ }\mu\text{s}$, Fig. Zth(J-mb))	I_{FRM}	20	A
Non-Repetitive Peak Forward Surge Current (10 ms, Single Sine-Wave Pulse)	I_{FSM}	60	A
Total Power Dissipation	P_{tot}	107.1	W
Operating Junction Temperature Range	T_J	-55 to +175	°C
Storage Temperature	T_{STG}	-55 to +175	°C

Thermal Characteristics

Parameter	Symbol	Condition or Model	Min.	Typ.	Max.	Unit
Thermal Resistance	Junction to Ambient	$R_{\theta(J-A)}$	In ambient air		60	°C/W
	Junction to Mounting Base	$R_{\theta(J-mb)}$	Transient thermal impedance curves		1.15	1.4

Electrical Characteristics (@ $T_J = 25\text{ °C}$ Unless Otherwise Noted)

Parameter	Symbol	Condition or Model	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 10\text{ A}$, $T_J = 25\text{ °C}$ $I_F = 10\text{ A}$, $T_J = 175\text{ °C}$		1.45 2.0	1.7 2.3	V
Reverse Leakage Current	I_R	$V_R = 650\text{ V}$, $T_J = 25\text{ °C}$ $V_R = 650\text{ V}$, $T_J = 175\text{ °C}$		0.5 25	50 250	μA
Recovered Charge	Q_r	$dI_F/dt = 500\text{ A}/\mu\text{s}$, $V_R = 400\text{ V}$, $I_F = 10\text{ A}$		14.5		nC
Diode Capacitance	C_d	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$		323		pF
Capacitance Stored Energy	E_c	$V_R = 400\text{ V}$		3.4		μJ



WARNING Cancer and Reproductive Harm - www.P65Warnings.ca.gov

*RoHS Directive 2015/863, Mar 31, 2015 and Annex.

**Bourns considers a product to be "halogen free" if (a) the Bromine (Br) content is 900 ppm or less; (b) the Chlorine (Cl) content is 900 ppm or less; and (c) the total Bromine (Br) and Chlorine (Cl) content is 1500 ppm or less.

Specifications are subject to change without notice.

Users should verify actual device performance in their specific applications.

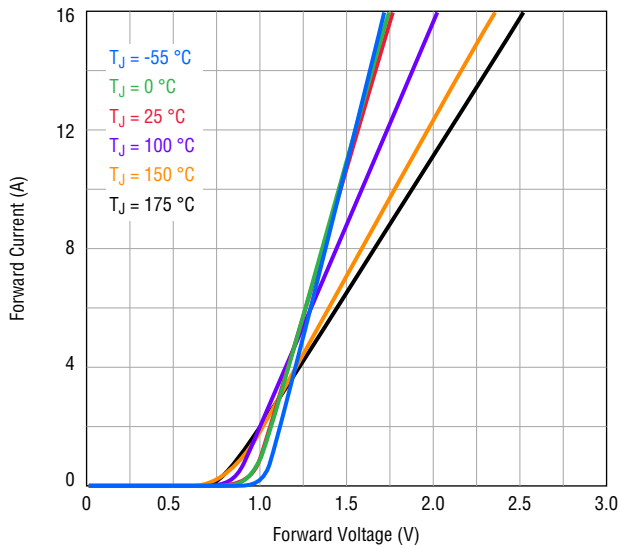
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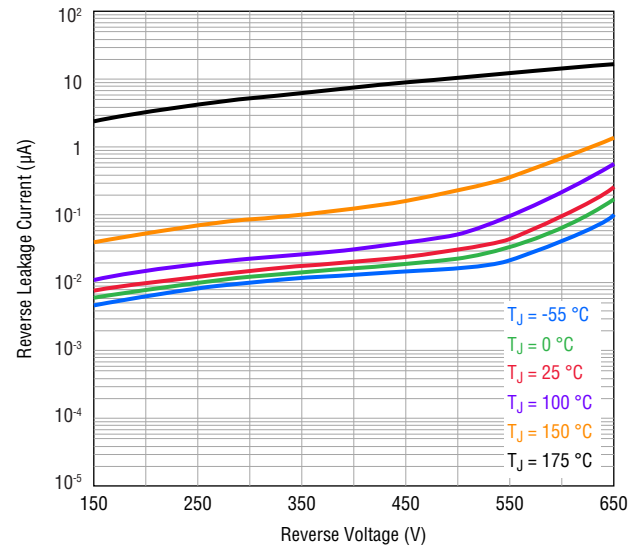
BOURNS®

Rating and Characteristic Curves ($T_J = 25^\circ\text{C}$ unless otherwise noted)

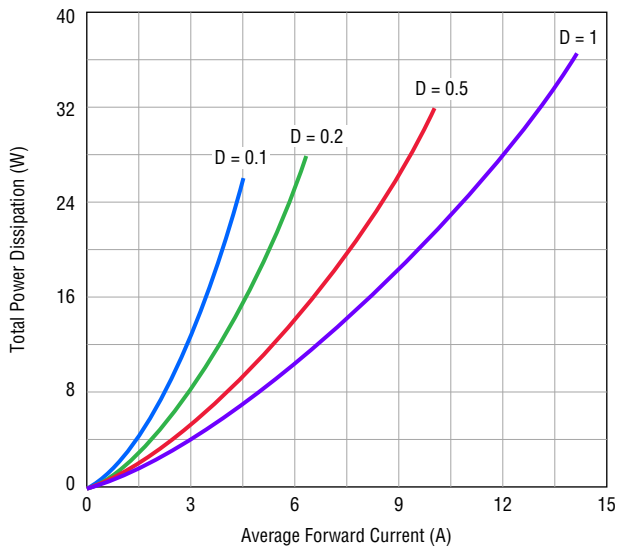
Typical Forward Characteristics



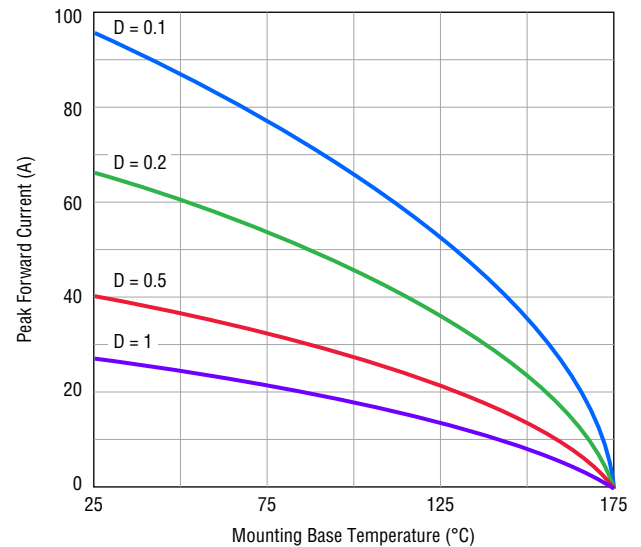
Typical Reverse Characteristics



Forward Power Dissipation



Forward Current Derating



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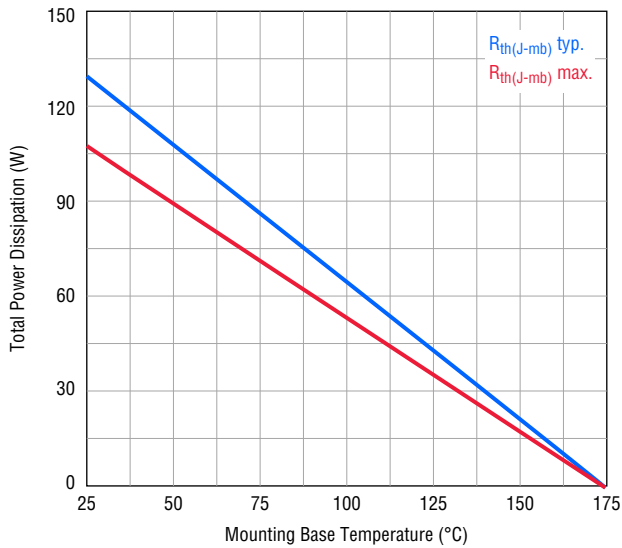
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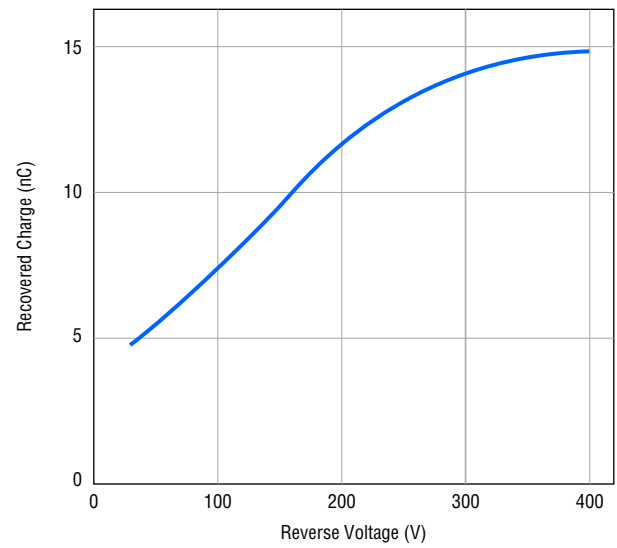
BOURNS®

Rating and Characteristic Curves (Continued)

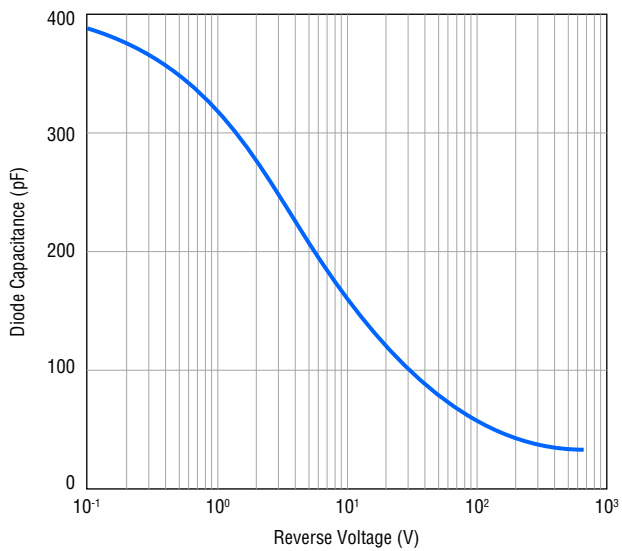
Power Derating



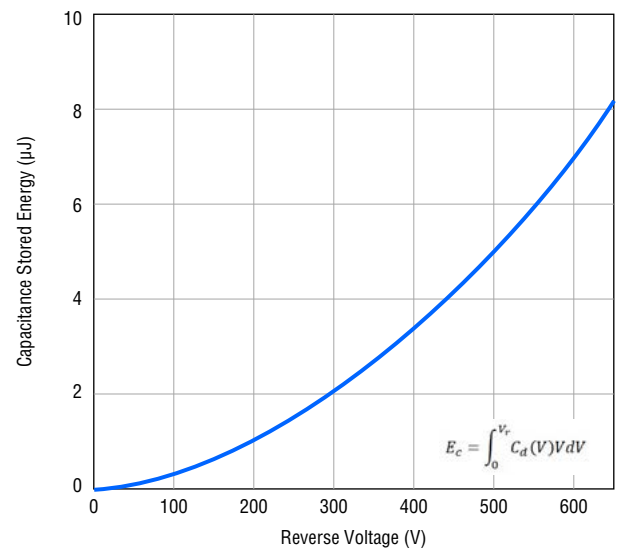
Typical Recovered Charge vs V_R



Typical Diode Capacitance vs V_R



Typical Capacitance Stored Energy vs V_R



Specifications are subject to change without notice.

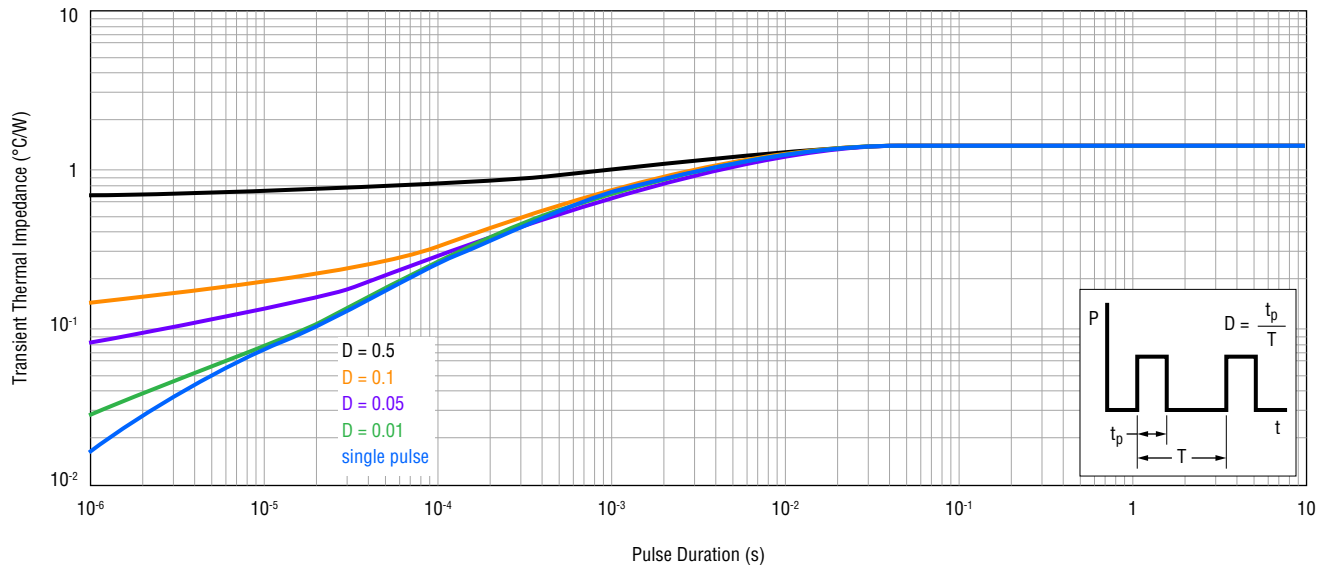
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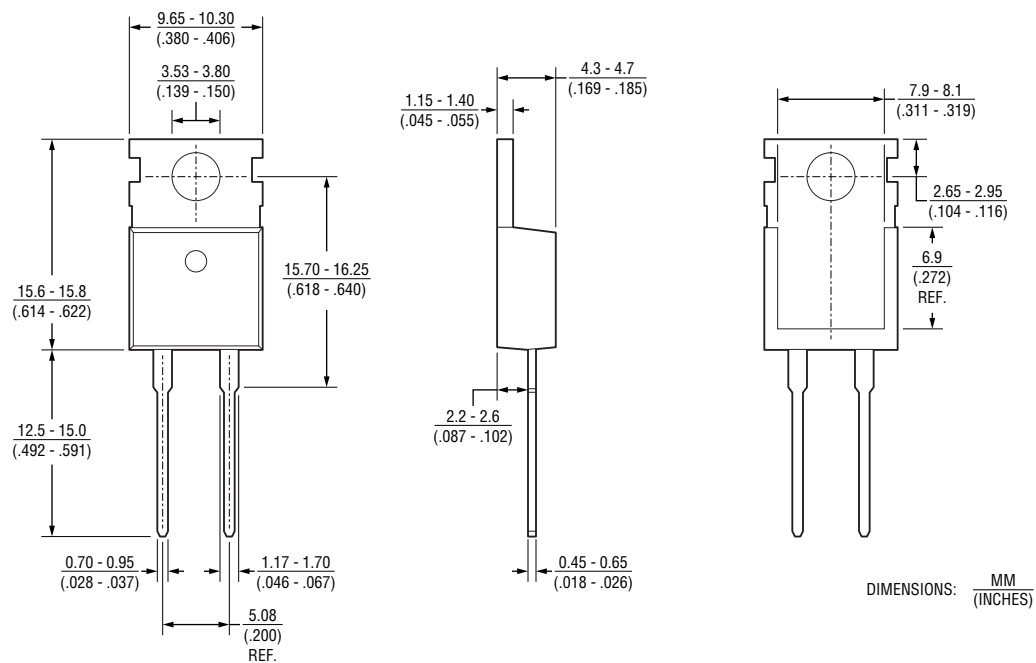
BOURNS®

Transient Thermal Impedance, $Z_{th}(J-mb)$



Product Dimensions

Package: TO220-2



Specifications are subject to change without notice.

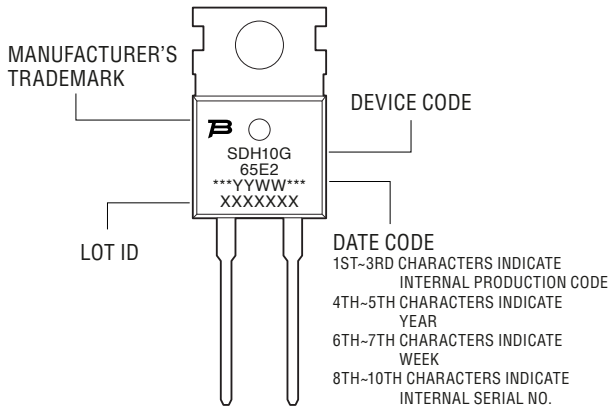
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BSDH10G65E2 Silicon Carbide Schottky Diode

BOURNS®

Typical Part Marking



Environmental Specifications

ESD Classification (HBM).....3B

How to Order

B SD H 10 G 65 E 2

Manufacturer _____
B = Bourns

Product Type _____
SD = SiC Diodes

Package Code _____
H = TO220-2

Current Rating _____
10 = 10 A

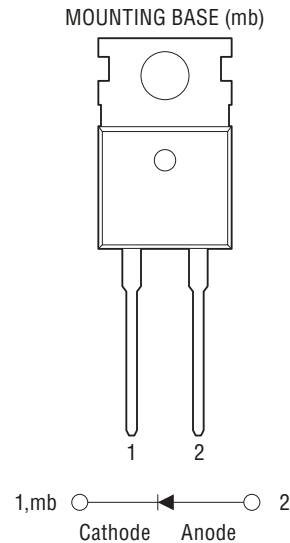
Device Type _____
G = General V_F

Nominal Voltage _____
65 = 650 V

Configuration _____
E = Single Diode

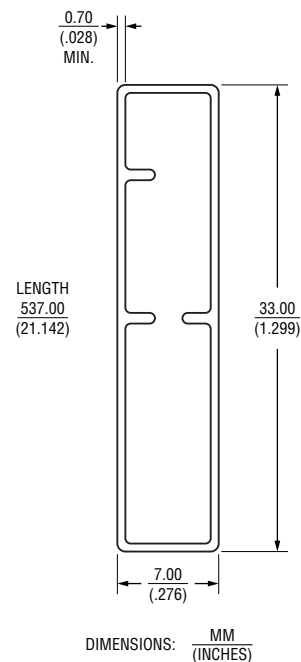
Version Number _____

Pin Information



Packaging Specifications

50 pcs./tube



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Email: eurocus@bourns.com

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